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# TECHNICAL REPORT

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**Process management for avionics - Electronic components capability in operation -**
**Part 2: Semiconductor microcircuit lifetime**

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# Process management for avionics - Electronic components capability in operation - Part 2: Semiconductor microcircuit lifetime

## FOREWORD

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This redline version of the official IEC Standard allows the user to identify the changes made to the previous edition IEC TR 62240-2:2018. A vertical bar appears in the margin wherever a change has been made. Additions are in green text, deletions are in strikethrough red text.

IEC TR 62240-2, which is a Technical Report, has been prepared by IEC technical committee 107: Process management for avionics. It is a Technical Report.

This second edition cancels and replaces the first edition published in 2018. This edition constitutes a technical revision.

This edition includes the following significant technical changes with respect to the previous edition:

a) introduction of an additional alternative path and approach where lifetime is assessed by the original component manufacturer based on user or original equipment manufacturer microcircuit mission profile;
b) update of Figure 1 with regard to the introduction of the additional alternative path & approach;
c) removal of the mention of SiC & GaN technologies from the considerations in 4.2.2 as the Scope indicates that the principles (process and method) described in this document can be applied to all types of semiconductor technologies.

The text of this Technical Report is based on the following documents:

| Draft | Report on voting |
|---|---|
| 107/447/DTR | 107/449/RVDTR |

Full information on the voting for its approval can be found in the report on voting indicated in the above table.

The language used for the development of this Technical Report is English.

This document was drafted in accordance with ISO/IEC Directives, Part 2, and developed in accordance with ISO/IEC Directives, Part 1 and ISO/IEC Directives, IEC Supplement, available at www.iec.ch/members_experts/refdocs. The main document types developed by IEC are described in greater detail at www.iec.ch/publications.

A list of all parts in the IEC 62240 series, published under the general title *Process management for avionics - Electronic components capability in operation*, can be found on the IEC website.

The committee has decided that the contents of this document will remain unchanged until the stability date indicated on the IEC website under webstore.iec.ch in the data related to the specific document. At this date, the document will be

– reconfirmed,
– withdrawn, or
– revised.

# INTRODUCTION

Electronic equipment for aerospace, defence and high performance (ADHP) applications integrates more and more commercial off the shelf (COTS) semiconductor microcircuits. These semiconductor microcircuits are above all designed and produced to address high volume and low cost markets such as consumer electronics, telecommunications or microcomputers, whose main requirements are basically cost, integration, performance and low consumption and for which the long term reliability in severe environments (for example vibration, thermal cycling, humidity and operating temperature) is not necessarily an imperative design criterion.

With semiconductor transistor feature size decrease, mainly from 90 nm transistor feature size, wear-out can arise in COTS semiconductor microcircuits. For example, non-homothetic evolution of semiconductor microcircuit bias voltage and transistor feature size scaling have led to an increase of the electrical fields inside the semiconductor microcircuit and hence changes in classical failure and degradation modes or mechanisms. In addition new transistor architectures and technologies (for example fin field effect transistor (FinFET), fully depleted silicon on insulator (FD-SOI), etc.) and new materials (for example low-k dielectrics, high-k dielectrics, strain source/drain Si-Ge) have been introduced since the generation 90 nm, and particularly from 45 nm and below, to overcome the scaling issues, contributing potentially to the evolution of failure and degradation modes or mechanisms.

In this context, it might not be possible for the lifetime of new generations of COTS semiconductor microcircuits ~~may not~~ to meet the lifetime requirements of high performance, high reliability and long duration electronic applications (for example twenty years, thirty years or more). As a consequence, specific reliability assessment and maintenance plans are considered within the semiconductor microcircuit selection activities.

## 1 Scope

This part of IEC 62240, which is a Technical Report, focuses on original equipment manufacturers (OEMs) using commercial off the shelf (COTS) semiconductor microcircuits for high performance, high reliability and long duration applications. This document supports OEMs in the preparation and maintenance of their semiconductor electronic component management plan (ECMP).

NOTE 1 OEMs are responsible for applications reliability performance that semiconductor microcircuit lifetime can affect; They are thus responsible for the compliance of the lifetime of the semiconductor microcircuits they use with the lifetime requirements of the microcircuits under the applications mission conditions.

This document describes a process and a method for selecting digital semiconductor microcircuits by ensuring that their lifetime is compatible with the requirements of aerospace, defence and high performance (ADHP) applications (generally in connection with functional environments). Methods and guidelines are provided to assess the long-term reliability of COTS semiconductor microcircuits in such applications; they mainly apply during the electronic design phase when selecting semiconductor microcircuits and assessing the application reliability.

Moreover, this document focuses on the intrinsic wear-out and the lifetime of COTS semiconductor microcircuits processed of less than or equal to 90 nm feature size (also called deep sub-micron (DSM) semiconductor microcircuits) and puts aside, at this time, packaging wear-out and random failure mechanisms. In this view, physics of failure (PoF) is at the heart of the approach.

Indeed 90 nm process node was a bend for realizing that the semiconductor wear-out and lifetime was a concern for microcircuits processed with nodes from 90 nm and below with regard to aerospace, defence and high performance (ADHP) mission profile.

Particularly from 45 nm and below, wear-out and lifetime remains a serious concern for long term ADHP missions. In addition, from 28 nm, scaling is no longer a classical technology shrink (case of planar technology for example) and different technological architectures of transistors are introduced (for example: fin field-effect transistors (FinFETs), gate-all-around field-effect transistors (GAAFETs)); semiconductor microcircuits in such technologies are often named ultra-deep sub-micron (UDSM).

Although developed for COTS deep sub-micron (DSM) semiconductor microcircuits based on silicon, the high-level approach and principles (process and method) described in this document can apply to all types of devices technologies, for example devices processed with a gallium nitride (GaN) technology or a silicon carbide (SiC) technology.

NOTE 2 IEC 62239-1 can assist OEMs in the creation and maintenance of ECMPs.

NOTE 3 SAE ARP6338 can also help the OEM with regard to assessment and mitigation of wear-out of life-limited semiconductor microcircuits.

NOTE 4 With the evolution of electronic technology and semiconductor microcircuits processed of less than or equal to 90 nm feature size, the current MIL-HDBK-217 handbook or FIDES guide become inappropriate as they are based for the time being on the assumption that the semiconductor electronic component exhibits a constant (random) failure rate and does not have life limits or exhibit wear-out.

Moreover, silicon itself has fundamentally very low failures in time (FIT) rates and the major failure modes are often in the packaging (for example housing, bond wires, etc.).

Although developed for the avionics industry, this process can be applied by other industrial sectors.

## 2 Normative references

There are no normative references in this document.

# 3 Terms, definitions and abbreviated terms

## 3.1 Terms and definitions

For the purposes of this document, the following terms and definitions apply.

ISO and IEC maintain terminology databases for use in standardization at the following addresses:

– IEC Electropedia: available at https://www.electropedia.org/

– ISO Online browsing platform: available at https://www.iso.org/obp

**3.1.1**
**acceleration model**
equation for predicting time-to-fail as a function of operating stress

Note 1 to entry: An acceleration model shows how time-to-fail at a particular operating stress level can be used to predict the equivalent time-to-fail at a different operating stress level.

Note 2 to entry: An acceleration model is associated to one failure and degradation mode or mechanism. Acceleration models can be either defined for temperature, electrical, mechanical, environmental, or other stresses that can affect the reliability of a device.

Note 3 to entry: An acceleration model is semi-empirical and is basically based on the physics of failure. Times are generally derived from modeled time-to-failure distributions (lognormal, Weibull, exponential, etc.).

Note 4 to entry: The acceleration model is also defined as acceleration factor, for which the abbreviated term AF is used.

~~**3.1.2**~~
~~**Bi-CMOS**~~
~~**bipolar CMOS**~~
~~technology integrating two separate semiconductor technologies, bipolar junction transistor and CMOS transistor, in a single electronic component~~

**3.1.2**
**cold redundancy**
technique where one primary part is operational and the redundant one is in a backup mode

Note 1 to entry: The redundant part can also be called "cold" part and generally it is technically identical to the primary part.

Note 2 to entry: The "cold" part can be non-powered or in a standby mode and it is usually called upon only on failure of the primary part.

**3.1.3**
**electronic equipment**
functioning electronic device produced by the plan owner, which incorporates electronic components

Note 1 to entry: End items, sub-assemblies, line-replaceable units and shop-replaceable units are examples of electronic equipment.

[SOURCE: IEC 62239-1:2018, 3.1.20]

**3.1.4**
**high-k dielectrics**
material with a high dielectric constant "k" (as compared to silicon dioxide)

Note 1 to entry: High-k dielectrics are used in semiconductor manufacturing processes where they are usually used to replace a silicon dioxide gate dielectric or another dielectric layer of a semiconductor microcircuit. The implementation of high-k gate dielectrics is one of several strategies developed to allow continued scaling and miniaturization of semiconductor microcircuits.